

**IN THE CLAIMS**

1. – 24. (Cancelled)

25. (New) A method for the formation of rectifying junctions on alloy-semiconductors comprising the steps of:

photo-electrochemical removal of one component of the alloy material and  
chemical etching of another component of the alloy to produce a positive-  
intermediate-negative (PIN) structure semiconductor.

26. (New) The method according to Claim 25, wherein the alloy semiconductor comprises a combination of Group II element and a Group VI element.

27. (New) The method according to Claim 26, wherein the alloy semiconductor comprises CdTe.

28. (New) The method according to Claim 26, wherein the alloy semiconductor comprises CdZnTe.

29. (New) The method according to Claim 26, wherein the alloy semiconductor comprises HgZnCdTe.

30. (New) The method according to Claim 26, wherein the alloy semiconductor comprises HgCdZnSe.

31. (New) A method for forming an N-type contact on an alloy-semiconductor material comprising a compound having at least a first component, the method comprising:

photo-electrochemical removal of the first component to form the N-type contact;

wherein photo-electrochemical removal of the first component comprises

depositing a removable N-type conductive material comprising an Hg-In eutectic paste on the alloy-semiconductor material;

connecting the deposited material to a negative terminal of a power supply;

connecting an electrode disposed in an electrolyte solution to a positive terminal of the power supply; and

exposing the electrolyte solution to a light source.

32. (New) The method according to claim 31, wherein the first component comprises a Group VI element.

33. (New) The method according to claim 32, wherein the compound is selected from the group consisting of CdTe, CdZnTe, and HgZnCdTe.

34. (New) The method according to claim 31, wherein the light source comprises a near infrared wavelength light and has a median energy equal to the band gap of the alloy-semiconductor material.

35. (New) The method according to claim 31, wherein the electrolyte solution comprises a pH of at least about 10.5.

36. (New) The method according to claim 31, further comprising forming a P-type contact on the alloy-semiconductor material.

37. (New) The method according to claim 36, wherein the step of forming a P-type contact comprises metal deposition.

38. (New) The method according to claim 37, further comprises depositing a P-type metal on the P-type contact.

39. (New) The method according to claim 38, wherein the step of depositing the P-type metal comprises depositing the P-type metal by vacuum deposition or electrodeless chemical exchange.

40. (New) The method according to claim 36, wherein the alloy-semiconductor material further comprises a second component, the second component a complimentary component of the first component, the method further comprising removing the second component to form the P-type contact.

41. (New) The method according to claim 40, wherein the step of removing the second component comprises chemical etching.

42. (New) The method according to claim 41, further comprising exposing an area of the alloy-semiconductor material comprising the P-type contact to a retarding electrochemical potential to etch the second component at a faster rate than the first component.

43. (New) The method according to claim 41, wherein the step of removing the second component by chemical etching comprises exposing the alloy-semiconductor material to an oxidizing agent comprising nitric acid and phosphoric acid.

44. (New) The method according to claim 43, wherein the nitric acid is present in an amount from about 0.1% to about 0.5% by volume.

45. (New) The method according to claim 43, wherein the oxidizing agent comprises a solution of HNO<sub>3</sub>, distilled H<sub>2</sub>O, and H<sub>3</sub>PO<sub>4</sub>, in a ratio of 2:33:85 by volume.